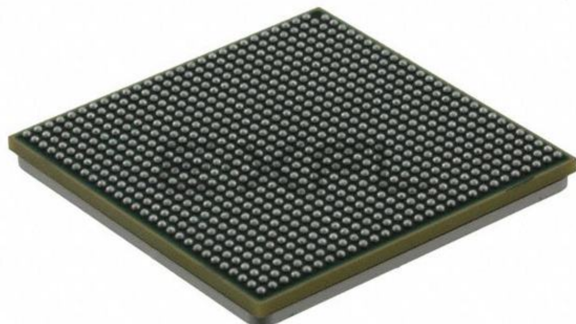

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	-
RAM Controllers	DDR2, DDR3
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (1)
USB	USB 2.0 (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8535avtanga

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DETAIL C

	A	B	C	D	E	F	G	H	J	K	L	M	N	P
15	MDQ [26]	MDQ [31]	GND	GV_{DD}	GND	GV_{DD}	GND	MDIC [0]	GND	MDIC [1]	GND	VDD_ CORE	GND	VDD_ CORE
16	MDQ [30]	MDQS [3]	MDQ [19]	MDQ [23]	MDQ [18]	GND	LCS [4]	LCS5/ DMA_ DREQ2	LCS6/ DMA_ DACK2	LA [28]	VDD_ CORE	GND	VDD_ CORE	GND
17	MDQS [3]	MDM [3]	GV_{DD}	GND	MDQS [2]	MDQ [22]	LA [31]	LA [30]	GND	LA [29]	GND	VDD_ PLAT	GND	VDD_ PLAT
18	MDQ [25]	MDQ [24]	MDQS [2]	MDM [2]	GV_{DD}	MDQ [21]	GND	LGPL3/ LFWP	BV_{DD}	LCS [0]	LCS7/ DMA_ DDONE2	GND	VDD_ PLAT	GND
19	MDQ [29]	MDQ [28]	NC	MDQ [17]	MDQ [16]	MDQ [20]	LCS [1]	LCS [2]	BV_{DD}	LGPL5	LA [27]	VDD_ PLAT	GND	VDD_ PLAT
20	MDQ [11]	MDQ [10]	GND	GV_{DD}	GND	BV_{DD}	LGPL2/ LOE/ LFRE	LCS [3]	LGPL0/ LFCLE	LGPL1/ LFALE	LGPL4/ LGTA/ LUPWAIT/ LPBSE/ LFRB	XGND	SD1_TX [1]	XV_{DD}
21	MDQ [15]	MDQ [14]	GV_{DD}	MDQ [3]	MDQ [7]	GND	LAD [31]	LWE[3]/ LBS[3]	BV_{DD}	GND	LAD [1]	XV_{DD}	SD1_TX [1]	XGND
22	MDQS [1]	MDQS [1]	MDQ [2]	MDQ [6]	GV_{DD}	LAD [29]	LAD [30]	LWE[1]/ LBS[1]	LWE0/ LBS0/ LFWE	LAD [0]	LAD [2]	SD1_TX [0]	XGND	SD1_TX [2]
23	MDQ [9]	MDM [1]	MDQS [0]	GND	LAD [27]	BV_{DD}	LAD [28]	LWE[2]/ LBS[2]	BV_{DD}	LAD [3]	BV_{DD}	SD1_TX [0]	XV_{DD}	SD1_TX [2]
24	MDQ [8]	MDQ [13]	GV_{DD}	MDQS [0]	LAD [24]	LAD [23]	LAD [26]	LCLK [0]	LCLK [1]	LAD [4]	LAD [5]	XGND	NC	SGND
25	MDQ [12]	MDQ [5]	MDM [0]	MDQ [4]	LDP [3]	LAD [19]	GND	LCLK [2]	LBCTL	LAD [7]	LAD [6]	NC	SV_{DD}	SD1_RX [1]
26	MDQ [0]	MDQ [1]	LAD [25]	GND	LAD [22]	LAD [18]	LAD [16]	BV_{DD}	LALE	LDP [0]	GND	SD1_ IMP_CAL _RX	SGND	SD1_RX [1]
27	GND	LDP [2]	GND	LSYNC_ IN	LAD [21]	GND	LAD [15]	LAD [14]	GND	LAD [11]	LAD [9]	SV_{DD}	SD1_RX [0]	SGND
28	MVREF	GND	AVDD_ LBIU	LSYNC_ OUT	LAD [20]	LAD [17]	LDP [1]	LAD [13]	LAD [12]	LAD [10]	LAD [8]	SGND	SD1_RX [0]	SV_{DD}

Figure 5. Chip Pin Map Detail C

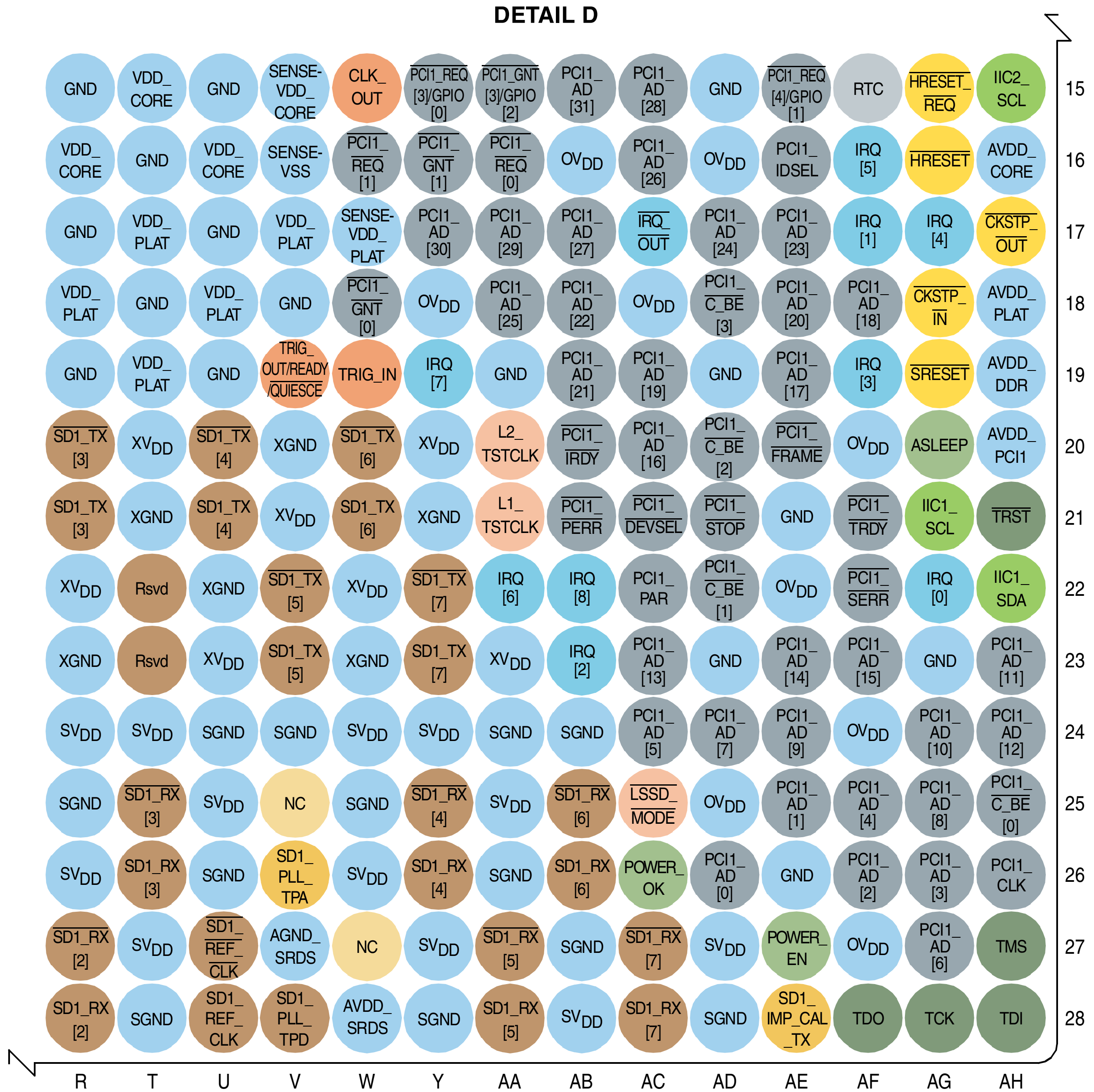


Figure 6. Chip Pin Map Detail D

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
LAD[0:31]	Muxed data / address	K22,L21,L22,K23,K24, L24,L25,K25,L28,L27, K28,K27,J28,H28,H27, G27,G26,F28,F26,F25, E28,E27,E26,F24,E24, C26,G24,E23,G23,F22, G22,G21	I/O	BV_{DD}	5,9,29
LDP[0:3]	Data parity	K26,G28,B27,E25	I/O	BV_{DD}	29
LA[27]	Burst address	L19	O	BV_{DD}	5,9,29
LA[28:31]	Port address	K16,K17,H17,G17	O	BV_{DD}	5,7,9,29
$\overline{\text{LCS}}$[0:4]	Chip selects	K18,G19,H19,H20,G16	O	BV_{DD}	29
$\overline{\text{LCS5}}$/$\overline{\text{DMA_DREQ2}}$	Chips selects / DMA Request	H16	I/O	BV_{DD}	1,29
$\overline{\text{LCS6}}$/$\overline{\text{DMA_DACK2}}$	Chips selects / DMA Ack	J16	O	BV_{DD}	1,29
$\overline{\text{LCS7}}$/$\overline{\text{DMA_DDONE2}}$	Chips selects / DMA Done	L18	O	BV_{DD}	1,29
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/$\overline{\text{LFWE}}$	Write enable / Byte select	J22	O	BV_{DD}	5,9,29
$\overline{\text{LWE[1:3]}}$/$\overline{\text{LBS[1:3]}}$	Write enable / Byte select	H22,H23,H21	O	BV_{DD}	5,9,29
LBCTL	Buffer control	J25	O	BV_{DD}	5,8,9,29
LALE	Address latch enable	J26	O	BV_{DD}	5,8,9,29
LGPL0/LFCLE	UPM general purpose line 0 / FLash command latch enable	J20	O	BV_{DD}	5,9,29
LGPL1/LFALE	UPM general purpose line 1 / Flash address latch enable	K20	O	BV_{DD}	5,9,29
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LFRE}}$	UPM general purpose line 2 / Output enable/Flash read enable	G20	O	BV_{DD}	5,8,9,29
LGPL3/$\overline{\text{LFWP}}$	UPM general purpose line 3 / Flash write protect	H18	O	BV_{DD}	5,9,29
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT /LPBSE/LFRB	UPM general purpose line 4 / Target Ack/Wait/SDRAM parity byte select/Flash Ready-busy	L20	I/O	BV_{DD}	29, 35
LGPL5	UPM general purpose line 5 / Amux	K19	O	BV_{DD}	5,9,29
LCLK[0:2]	Local bus clock	H24,J24,H25	O	BV_{DD}	29
LSYNC_IN	Synchronization	D27	I	BV_{DD}	29
LSYNC_OUT	Local bus DLL	D28	O	BV_{DD}	29
DMA					
$\overline{\text{DMA_DACK}}$[0:1] /GPIO[10:11]	DMA Acknowledge	AD6,AE10	O	OV_{DD}	—

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
DMA_DREQ[0:1] /GPIO[14:15]	DMA Request	AB10,AD11	I	OV_{DD}	—
DMA_DDONE[0:1] /GPIO[12:13]	DMA Done	AA11,AB11	O	OV_{DD}	—
DMA_DREQ[2]/LCS[5]	Chips selects / DMA Request	H16	I/O	BV_{DD}	1,29
DMA_DACK[2]/LCS[6]	Chips selects / DMA Ack	J16	O	BV_{DD}	1,29
DMA_DDONE[2]/LCS[7]	Chips selects / DMA Done	L18	O	BV_{DD}	1,29
DMA_DREQ[3]/IRQ[9]	External interrupt/DMA request	AE13	I	OV_{DD}	1
DMA_DACK[3]/IRQ[10]	External interrupt/DMA Ack	AD13	I/O	OV_{DD}	1
DMA_DDONE[3]/IRQ[11]	External interrupt/DMA done	AD14	I/O	OV_{DD}	1
USB Port 1					
USB1_D[7:0]	USB1 Data bits	AF1,AE2,AE1,AD2, AC2,AC1,AB2,AB1	I/O	OV_{DD}	—
USB1_NXT	USB1 Next data	AF2	I	OV_{DD}	—
USB1_DIR	USB1 Data Direction	AH1	I	OV_{DD}	—
USB1_STP	USB1 Stop	AG1	O	OV_{DD}	5,9
USB1_PWRFAULT	USB1 bus power fault.	AH2	I	OV_{DD}	—
USB1_PCTL0/GPIO[6]	USB1 Port control 0	AC3	O	OV_{DD}	—
USB1_PCTL1/GPIO[7]	USB1 Port control 1	AC4	O	OV_{DD}	—
USB1_CLK	USB1 bus clock	AD1	I	OV_{DD}	—
USB Port 2					
USB2_D[7:0]	USB2 Data bits	AE6,AC6,AF5,AE5, AF4,AE4,AE3,AD3	I/O	OV_{DD}	—
USB2_NXT	USB2 Next data	AC7	I	OV_{DD}	—
USB2_DIR	USB2 Data Direction	AF7	I	OV_{DD}	—
USB2_STP	USB2 Stop	AD7	O	OV_{DD}	5,9
USB2_PWRFAULT	USB2 bus power fault.	AC8	I	OV_{DD}	—
USB2_PCTL0/GPIO[8]	USB2 Port control 0	AG9	O	OV_{DD}	—
USB2_PCTL1/GPIO[9]	USB2 Port control 1	AC9	O	OV_{DD}	—
USB2_CLK	USB2 bus clock	AD5	I	OV_{DD}	—
—					
Reserved	—	AH8	—	—	—
Reserved	—	AH7,AG6,AH6,AG5, AG4,AH4,AG3,AH3, AG7, AG8, AH9,AH5	—	—	27

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes
TSEC3_TX_CLK	Transmit clock In	U10	I	TV_{DD}	—
TSEC3_GTX_CLK	Transmit clock Out	U5	O	TV_{DD}	—
TSEC3_CRS	Carrier sense	T10	I/O	TV_{DD}	17
TSEC3_COL	Collision detect	T9	I	TV_{DD}	—
TSEC3_RXD[7:0]	Receive data	U12,U13,U6,V6,V1,U3, U2,V3	I	TV_{DD}	—
TSEC3_RX_DV	Receive data valid	V2	I	TV_{DD}	—
TSEC3_RX_ER	Receive data error	T4	I	TV_{DD}	—
TSEC3_RX_CLK	Receive clock	U1	I	TV_{DD}	—
IEEE 1588					
TSEC_1588_CLK	Clock In	W9	I	LV_{DD}	29
TSEC_1588_TRIG_IN[0:1]	Trigger In	W8,W7	I	LV_{DD}	29
TSEC_1588_TRIG_OUT[0:1]	Trigger Out	U11,W10	O	LV_{DD}	5,9,29
TSEC_1588_CLK_OUT	Clock Out	V10	O	LV_{DD}	5,9,29
TSEC_1588_PULSE_OUT1	Pulse Out1	V11	O	LV_{DD}	5,9,29
TSEC_1588_PULSE_OUT2	Pulse Out2	T11	O	LV_{DD}	5,9,29
eSDHC					
SDHC_CMD	Command line	AH10	I/O	OV_{DD}	29
$\overline{\text{SDHC_CD}}$/GPIO[4]	Card detection	AH11	I	OV_{DD}	—
SDHC_DAT[0:3]	Data line	AG12,AH12,AH13, AG11	I/O	OV_{DD}	29
SDHC_DAT[4:7] / SPI_CS[0:3]	8-bit MMC Data line / SPI chip select	AE8,AC10,AF9,AA10	I/O	OV_{DD}	29
SDHC_CLK	SD/MMC/SDIO clock	AG13	I/O	OV_{DD}	29
$\overline{\text{SDHC_WP}}$/GPIO[5]	Card write protection	AG10	I	OV_{DD}	1, 32
eSPI					
SPI_MOSI	Master Out Slave In	AF8	I/O	OV_{DD}	29
SPI_MISO	Master In Slave Out	AD9	I	OV_{DD}	29
SPI_CLK	eSPI clock	AD8	I/O	OV_{DD}	29
SPI_CS[0:3] / SDHC_DAT[4:7]	eSPI chip select / SDHC 8-bit MMC data	AE8,AC10,AF9,AA10	I/O	OV_{DD}	29
DUART					
$\overline{\text{UART_CTS}}$[0:1]	Clear to send	AE11,Y12	I	OV_{DD}	29
$\overline{\text{UART_RTS}}$[0:1]	Ready to send	AB12,AD12	O	OV_{DD}	29
UART_SIN[0:1]	Receive data	AC12,AF12	I	OV_{DD}	29

Table 1. Pinout Listing (continued)

Signal	Signal Name	Package Pin Number	Pin Type	Power Supply	Notes

Notes:

1. All multiplexed signals may be listed only once and may not re-occur.
2. Recommend a weak pull-up resistor (2–10 KΩ) be placed on this pin to OV_{DD}.
3. This pin must always be pulled-high.
4. This pin is an open drain signal.
5. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-kΩ pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pullup or active driver is needed.
6. Treat these pins as no connects (NC) unless using debug address functionality.
7. The value of LA[28:31] during reset sets the CCB clock to SYSCLK PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See Section 22.2, “CCB/SYSCLK PLL Ratio.”
8. The value of LALE, LGPL2 and LBCTL at reset set the e500 core clock to CCB Clock PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See the Section 22.3, “e500 Core PLL Ratio.”
9. Functionally, this pin is an output, but structurally it is an I/O because it either samples configuration input during reset or because it has other manufacturing test functions. This pin will therefore be described as an I/O for boundary scan.
10. For proper state of these signals during reset, UART_SOUT[1] must be pulled down to GND through a resistor. UART_SOUT[0] can be pulled up or left without a resistor. However, if there is any device on the net which might pull down the value of the net at reset, then a pullup is needed on UART_SOUT[0].
11. This output is actively driven during reset rather than being three-stated during reset.
12. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
13. These pins are connected to the V_{DD_CORE}/V_{DD_PLAT}/GND planes internally and may be used by the core power supply to improve tracking and regulation.
15. These pins have other manufacturing or debug test functions. It’s recommended to add both pull-up resistor pads to OVDD and pull-down resistor pads to GND on board to support future debug testing when needed.
16. If this pin is connected to a device that pulls down during reset, an external pull-up is required to drive this pin to a safe state during reset.
17. This pin is only an output in FIFO mode when used as Rx Flow Control.
18. Do not connect.
19. These must be pulled up (100 Ω- 1 kΩ) to OVDD.
20. Independent supplies derived from board VDD.
21. Recommend a pull-up resistor (1 KΩ) be placed on this pin to OV_{DD}.
22. The following pins must NOT be pulled down during power-on reset: MDVAL, UART_SOUT[0], EC_MDC, TSEC1_TXD[3], TSEC3_TXD[7], HRESET_REQ, TRIG_OUT/READY/$\overline{\text{QUIESCE}}$, MSRCID[2:4], ASLEEP.
23. This pin requires an external 4.7-kΩ pull-down resistor to prevent PHY from seeing a valid Transmit Enable before it is actively driven.
24. General-Purpose POR configuration of user system.

2.1.3 Output Driver Characteristics

This table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 4. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 35	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default) 125	BV_{DD} = 3.3 V BV_{DD} = 2.5 V BV_{DD} = 1.8 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	42 (default)		
DDR2 signal	16 32 (half strength mode)	GV_{DD} = 1.8 V	3
DDR3 signal	20 40 (half strength mode)	GV_{DD} = 1.5 V	2
TSEC signals	42	LV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	42	OV_{DD} = 3.3 V	—
I^2C	150	OV_{DD} = 3.3 V	—

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI1_GNT1}}$ signal at reset.
3. The drive strength of the DDR2 or DDR3 interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min)

2.2 Power Sequencing

The chip requires its power rails to be applied in a specific sequence in order to ensure proper chip operation. These requirements are as follows for power up:

1. V_{DD_PLAT}, V_{DD_CORE} (if POWER_EN is not used to control V_{DD_CORE}), AV_{DD}, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD},$S2V_{DD}$, TV_{DD}, XV_{DD} and $X2V_{DD}$
2. [Wait for POWER_EN to assert], then V_{DD_CORE} (if POWER_EN is used to control V_{DD_CORE})
3. GV_{DD}

All supplies must be at their stable values within 50 ms.

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

From a system standpoint, if any of the I/O power supplies ramp prior to the VDD platform supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the chip.

During the Deep Sleep state, the VDD core supply is removed. But all other power supplies remain applied. Therefore, there is no requirement to apply the VDD core supply before any other power rails when the silicon waking from Deep Sleep.

Table 17. DDR3 SDRAM Input AC Timing Specifications for 1.5-V Interface

At recommended operating conditions with GV_{DD} of 1.5 V ± 5%. DDR3 data rate is between 606MHz and 667MHz.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.175	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.175	—	V	—

Table 18. DDR2 and DDR3 SDRAM Interface Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8 V ± 5% for DDR2 or 1.5 V ± 5% for DDR3.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC	t_{CISKEW}	—	—	ps	1, 2
667 MHz	—	–240	240	—	3
533 MHz	—	–300	300	—	—
400 MHz	—	–365	365	—	—

Note:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: t_{DISKEW} =+/-(T/4 - abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. Maximum DDR2 and DDR3 frequency is 667MHz.

This figure shows the DDR2 and DDR3 SDRAM interface input timing diagram.

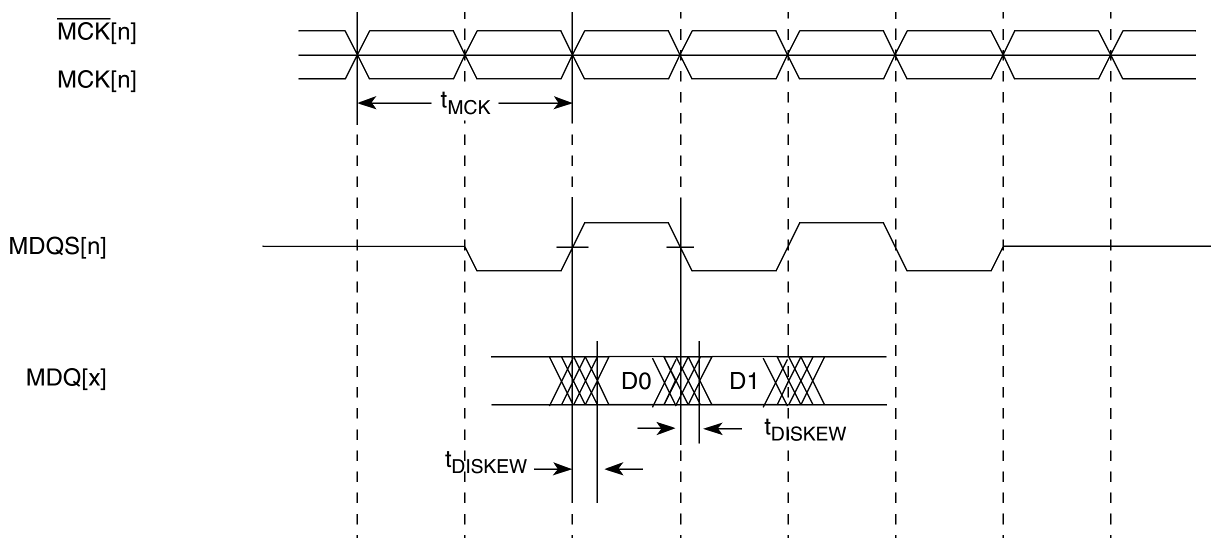


Figure 8. DDR SDRAM Input Timing Diagram

2.8 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the chip.

2.8.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface.

Table 22. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	– 0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

2.8.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface.

Table 23. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	CCB clock/1,048,576	baud	2
Maximum baud rate	CCB clock/16	baud	2,3
Oversample rate	16	—	4

Notes:

2. CCB clock refers to the platform clock.
3. Actual attainable baud rate will be limited by the latency of interrupt processing.
4. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

2.9 Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management

This section provides the AC and DC electrical characteristics for enhanced three-speed and MII management.

2.9.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps) — FIFO/GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics

The electrical characteristics specified here apply to all FIFO mode, gigabit media independent interface (GMII), media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), and reduced media independent interface (RMII) signals except management data input/output (MDIO) and management data clock (MDC), and serial gigabit media independent interface (SGMII). The RGMII, RTBI and FIFO mode interfaces are defined for 2.5 V, while the GMII, MII, RMII, and TBI interfaces can operate at 3.3V.

The GMII, MII, or TBI interface timing is compliant with IEEE 802.3. The RGMII and RTBI interfaces follow the Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3 (12/10/2000). The RMII interface follows the RMII Consortium RMII Specification Version 1.2 (3/20/1998).

The electrical characteristics for MDIO and MDC are specified in Section 2.10, "Ethernet Management Interface Electrical Characteristics."

The electrical characteristics for SGMII is specified in Section 2.9.3, "SGMII Interface Electrical Characteristics." The SGMII interface conforms (with exceptions) to the Serial-GMII Specification Version 1.8.

2.9.1.1 GMII, MII, TBI, RGMII, RMII and RTBI DC Electrical Characteristics

All GMII, MII, TBI, RGMII, RMII and RTBI drivers and receivers comply with the DC parametric attributes specified in the following tables. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 24. GMII, MII, RMII, and TBI DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.13	3.47	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, IOH = –4.0 mA)	VOH	2.40	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, IOL = 4.0 mA)	VOL	GND	0.50	V	—
Input high voltage	V_{IH}	1.90	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.90	V	—
Input high current ($V_{IN} = LV_{DD}$, $V_{IN} = TV_{DD}$)	I_{IH}	—	40	μA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–600	—	μA	3

Notes:

[1] LV_{DD} supports eTSECs 1.

[2] TV_{DD} supports eTSECs 3.

[3] The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

- — The external reference clock driver must be able to drive this termination.
- — The SerDes reference clock input can be either differential or single-ended. See the Differential Mode and Single-ended Mode description below for further detailed requirements.

- The maximum average current requirement that also determines the common mode voltage range
  - — When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (refer to the following bullet for more detail), since the input is AC-coupled on-chip.
  - — This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V/50 = 8 mA) while the minimum common mode input level is 0.1V above SnGND (xcorevss). For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0mA to 16mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800mV with the common mode voltage at 400mV.
  - — If the device driving the SD*n*_REF_CLK and $\overline{\text{SD}n\text{_REF_CLK}}$ inputs cannot drive 50 Ω to SnGND (xcorevss) DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.
- The input amplitude requirement
  - — This requirement is described in detail in the following sections.

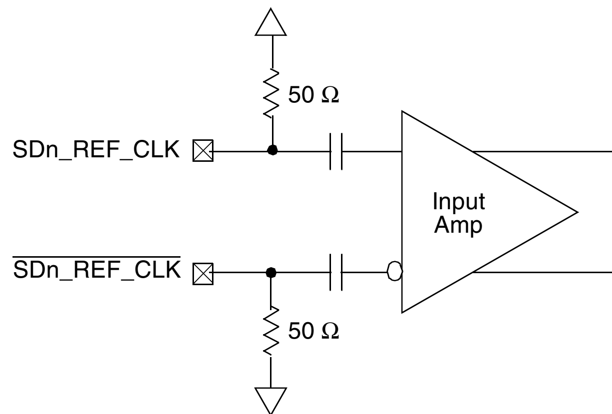


Figure 58. Receiver of SerDes Reference Clocks

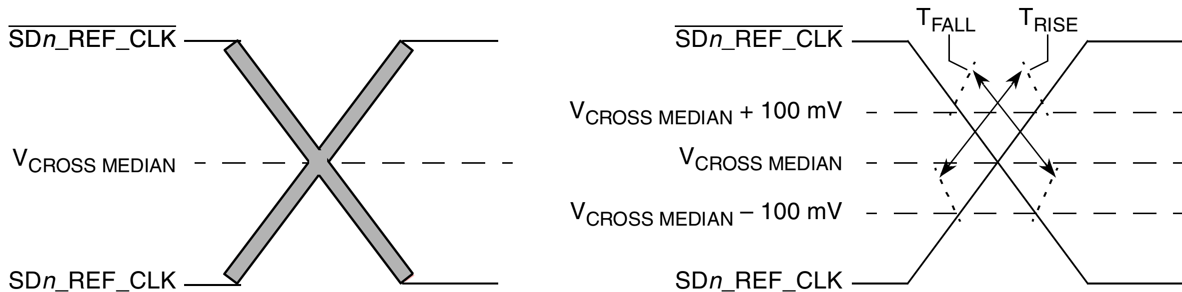


Figure 67. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes Reference Clocks is defined by each interface protocol based on application usage. See the following sections for detailed information:

- Section 2.9.3.2, “AC Requirements for SGMII SD2_REF_CLK and SD2_REF_CLK”
- Section 2.21.2, “AC Requirements for PCI Express SerDes Clocks”

2.20.2.4.1 Spread Spectrum Clock

SD1_REF_CLK/SD1_REF_CLK were designed to work with a spread spectrum clock (+0 to -0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation should be used.

SD2_REF_CLK/SD2_REF_CLK are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

2.20.3 SerDes Transmitter and Receiver Reference Circuits

This figure shows the reference circuits for SerDes data lane’s transmitter and receiver.

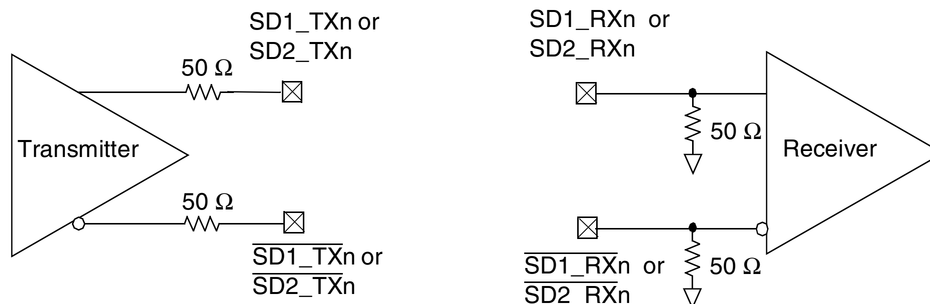


Figure 68. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below (PCI Express, SATA or SGMII) in this document based on the application usage:

- Section 2.9.3, “SGMII Interface Electrical Characteristics”
- Section 2.21, “PCI Express”
- Section 2.16, “Serial ATA (SATA)”

Please note that external AC Coupling capacitor is required for the above three serial transmission protocols with the capacitor value defined in specification of each protocol section.

2.21 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the chip.

2.21.1 DC Requirements for PCI Express SD1_REF_CLK and $\overline{\text{SD1_REF_CLK}}$

For more information, see Section 2.20.2, "SerDes Reference Clocks."

2.21.2 AC Requirements for PCI Express SerDes Clocks

This table lists AC requirements.

Table 70. SD1_REF_CLK and $\overline{\text{SD1_REF_CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typical	Max	Units	Notes
t_{REF}	REFCLK cycle time	—	10	—	ns	1
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location	–50	—	50	ps	1,2,3

Notes:
1. Tj at BER of 10E-6 86 ps Max.
2. Total peak-to-peak deterministic jitter "Dj" should be less than or equal to 42 ps.
3. Limits from "PCI Express CEM Rev 2.0" and measured per "PCI Express Rj, D, and Bit Error Rates".

2.21.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million 15 (ppm) of each other at all times. This is specified to allow bit rate clock sources with a +/– 300 ppm tolerance.

2.21.4 Physical Layer Specifications

The following is a summary of the specifications for the physical layer of PCI Express on this chip. For further details as well as the specifications of the transport and data link layer, please use the PCI Express Base Specification. REV. 1.0a document.

2.21.4.1 Differential Transmitter (TX) Output

This table defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

Table 71. Differential Transmitter (TX) Output Specifications

Symbol	Parameter	Min	Nom	Max	Units	Comments
UI	Unit Interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for Spread Spectrum Clock dictated variations. See Note 1.
$V_{TX-DIFFp-p}$	Differential Peak-to-Peak Output Voltage	0.8	—	1.2	V	$V_{TX-DIFFp-p} = 2*\|V_{TX-D+} - V_{TX-D-}\|$ See Note 2.

2.23.1 Clock Ranges

This table provides the clocking specifications for the processor cores and Table 74 provides the clocking specifications for the memory bus.

Table 73. Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency								Unit	Notes
	600 MHz		800 MHz		1000 MHz		1250 MHz			
	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	600	600	600	800	600	1000	600	1250	MHz	1, 2
CCB frequency	400	400	400	400	333	400	333	500		
DDR Data Rate	400	400	400	400	400	400	400	500		

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, "CCB/SYSCLK PLL Ratio," Section 2.23.3, "e500 Core PLL Ratio,"and Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
2. The processor core frequency speed bins listed also reflect the maximum platform (CCB) and DDR data rate frequency supported by production test. Running CCB and/or DDR data rate higher than the limit shown above, although logically possible via valid clock ratio setting in some condition, is not supported.

The DDR memory controller can run in either synchronous or asynchronous mode. When running in synchronous mode, the memory bus is clocked relative to the platform clock frequency. When running in asynchronous mode, the memory bus is clocked with its own dedicated PLL. This table provides the clocking specifications for the memory bus.

Table 74. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	600, 800, 1000, 1250			
	Min	Max		
DDR Memory bus clock speed	200	250	MHz	1, 2, 3, 4

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 2.23.2, "CCB/SYSCLK PLL Ratio," Section 2.23.3, "e500 Core PLL Ratio," and Section 2.23.4, "DDR/DDRCLK PLL Ratio," for ratio settings.
2. The Memory bus clock refers to the chip's memory controllers' MCK[0:5] and $\overline{\text{MCK}}$[0:5] output clocks, running at half of the DDR data rate.
3. In synchronous mode, the memory bus clock speed is half the platform clock frequency. In other words, the DDR data rate is the same as the platform (CCB) frequency. If the desired DDR data rate is higher than the platform (CCB) frequency, asynchronous mode must be used.
4. In asynchronous mode, the memory bus clock speed is dictated by its own PLL. See Section 2.23.4, "DDR/DDRCLK PLL Ratio." The memory bus clock speed must be less than or equal to the CCB clock rate which in turn must be less than the DDR data rate.

The recommended attachment method to the heat sink is illustrated in the following figure. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force (45 Newton).

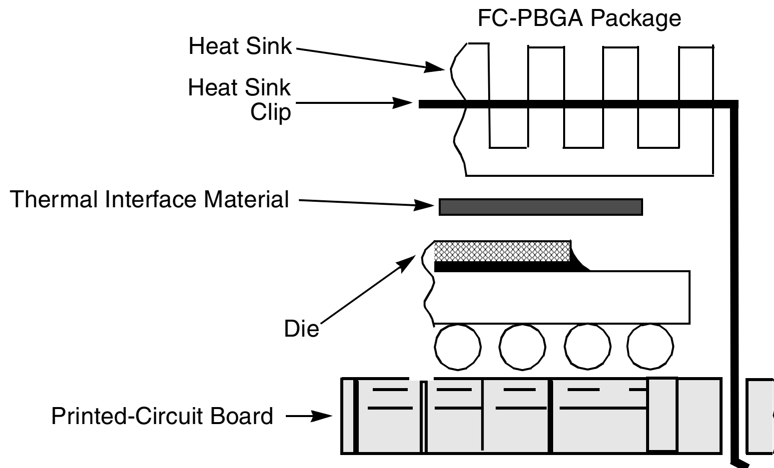


Figure 73. Package Exploded Cross-Sectional View with Several Heat Sink Options

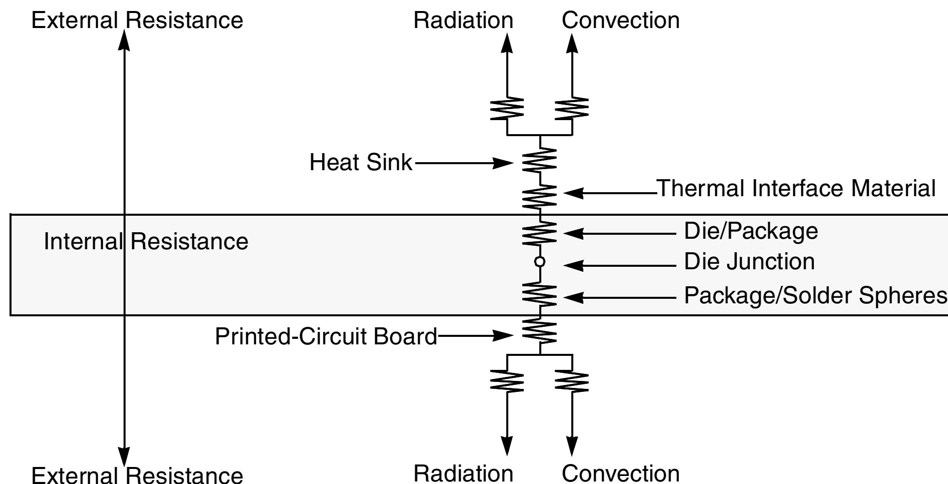
The system board designer can choose between several types of heat sinks to place on the chip. Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Advanced Thermal Solutions, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that will allow the chip to function in various environments.

2.24.3.1 Internal Package Conduction Resistance

For the packaging technology, shown in Table 70, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

This figure depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.



(Note the internal versus external package resistance)

Figure 74. Package with Heat Sink Mounted to a Printed-Circuit Board

These capacitors should have a value of 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values types and quantity of bulk capacitors.

3.5 SerDes Block Power Supply Decoupling Recommendations

he SerDes1 and SerDes2 blocks require a clean, tightly regulated source of power (SnV_{DD} and XnV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the chip. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the chip as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor from each SerDes supply (SnV_{DD} and XnV_{DD}) to the board ground plane on each side of the chip. This should be done for all SerDes supplies.
- Third, between the chip and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

3.6 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs should be tied to $V_{DD,}$$TV_{DD}$, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} as required. All unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected. Power and ground connections must be made to all external $V_{DD,}$$TV_{DD}$, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} and GND pins of the chip.

3.7 Pull-Up and Pull-Down Resistor Requirements

The chip requires weak pull-up resistors (2–10 kΩ is recommended) on open drain type pins including I^2C pins and MPIC interrupt pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 78. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion will give unpredictable results.

The following pins must NOT be pulled down during power-on reset: TSEC1_TXD[3], $\overline{\text{HRESET_REQ}}$, TRIG_OUT/READY/$\overline{\text{QUIESCE}}$, MSRCID[2:4], ASLEEP. The UART_SOUT[0:1] and $\overline{\text{TEST_SEL}}$ pins must be set to a proper state during POR configuration. Please refer to the pinlist table (see Table 62) of the individual chip for more details.

See the PCI 2.2 specification for all pull-ups required for PCI.

3.8 Output Buffer DC Impedance

The chip drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

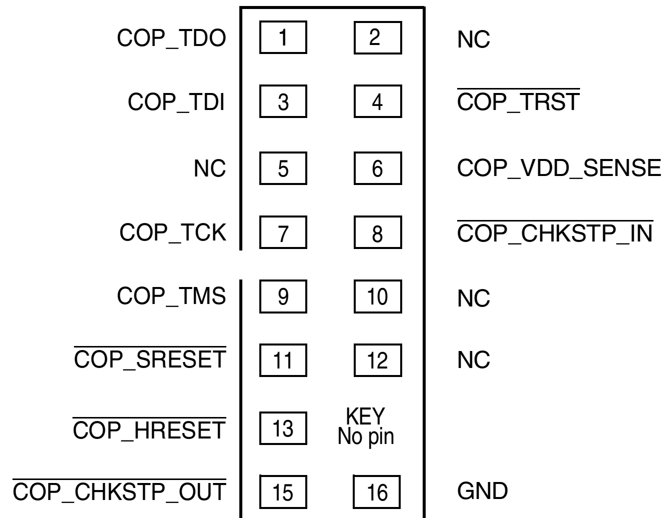


Figure 79. COP Connector Physical Pinout

3.11 Guidelines for High-Speed Interface Termination

3.11.1 SerDes1 Interface Entirely Unused

If the high-speed SerDes interface is not used at all, the unused pin should be terminated as described in this section. However, the SerDes must always have power applied to its supply pins. There are several reserved pins that need to be either left floating or connected to XGND. See SerDes1 in Table 1 for details.

The following pins must be left unconnected (float):

- SD1_TX[7:4]
- $\overline{\text{SD1_TX[7:4]}}$
- Reserved pins T22, T23

The following pins must be connected to XGND:

- SD1_RX[7:4]
- $\overline{\text{SD1_RX[7:4]}}$
- SD1_REF_CLK
- $\overline{\text{SD1_REF_CLK}}$

The POR configuration pin cfg_io_ports[0:2] on TSEC3_TXD[6:3] can be used to power down SerDes 1 block for power saving. Note that both SVDD and XVDD must remain powered.

3.11.2 SerDes 1 Interface Partly Unused

If only part of the high speed SerDes interface pins are used, the remaining high-speed serial I/O pins should be terminated as described in this section.

The following pins must be left unconnected (float) if not used:

- SD1_TX[7:4]
- $\overline{\text{SD1_TX[7:4]}}$
- Reserved pins: T22, T23

5.2 Mechanical Dimensions of the FC-PBGA

The mechanical dimensions and bottom surface nomenclature of the 783 FC-PBGA package are shown in the following figure.

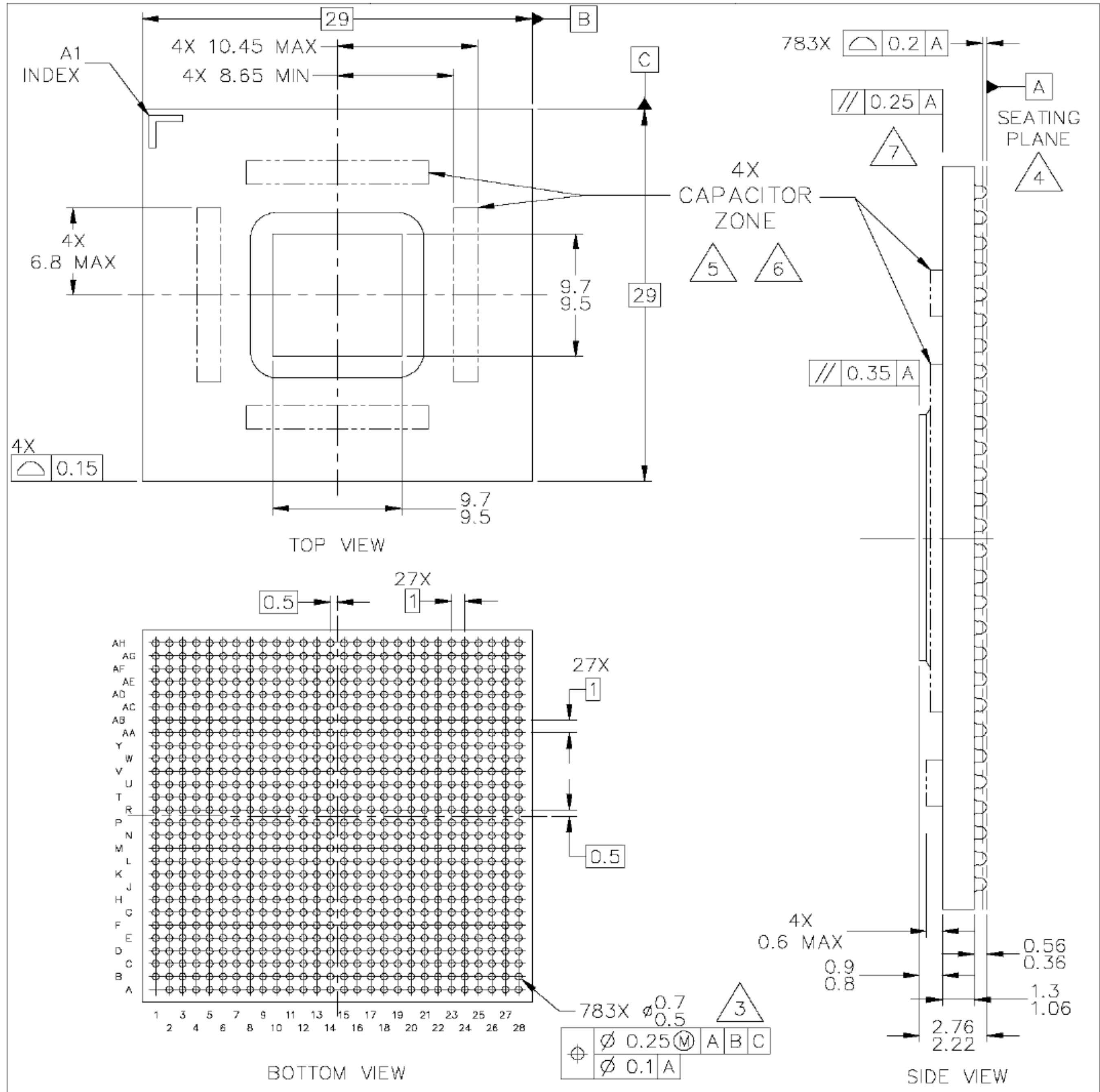


Figure 81. Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA

NOTES for Figure 81

1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

5. Capacitors may not be present on all devices
6. Caution must be taken not to short exposed metal capacitor pads on package top.
7. All dimensions are symmetric across the package center lines, unless dimensioned otherwise.

6 Product Documentation

The following documents are required for a complete description of the chip and are needed to design properly with the part.

- *MPC8536E PowerQUICC III Integrated Processor Reference Manual* (document number: MPC8536ERM)
- *e500 PowerPC Core Reference Manual* (document number: E500CORERM)

7 Document Revision History

This table provides a revision history for this hardware specification.

Table 85. Document Revision History

Revision	Date	Substantive Change(s)
5	09/2011	• Removed PVDD from Table 1, “Pinout Listing.”
4	06/2011	• In Table 1, “Pinout Listing,” updated the power supply for TSEC3 pins to TVDD. • Updated Table 56, “eSDHC AC Timing Specifications.” • In Section 4.3, “Part Numbering,” added an extra bin (1250/500/667) to support DDR3.
3	11/2010	• In Table 1, “Pinout Listing,” added the following note: “For systems that boot from Local Bus (GPCM)-controlled NOR flash or (FCM) controlled NAND flash, a pullup on LGPL4 is required...” In addition, updated footnote 26 and added footnote 29 to PCI1_AD. • Updated Table 21 • Updated Figure 25, “RGMII and RTBI AC Timing and Multiplexing Diagrams.” • In Table 44, “MII Management DC Electrical Characteristics,” changed the Voh/Vol values for MDIO/MDC. • Added Note 6 regarding USB*n*_DIR pin to Table 47, “USB General Timing Parameters6.” • In Table 64, “I2C AC Electrical Specifications,” updated footnote 2. • In Table 82, , Table 83, , Table 84, added the Revision Level A for Rev 1.2
2	09/2009	**Note:** • In Section 1, “Pin Assignments and Reset States,”updated the first sentence of the note to say, “The UART_SOUT[0:1] and TEST_SEL pins must be set to a proper state during POR configuration.” • In Table 40, “SGMII DC Receiver Electrical Characteristics,” changed LSTSAB to LSTSA and LSTSEF to LSTSE for Note 4. • Updated Die value and Bump/Underfill value in Table 84 **Note:** Updated Figure 81, “Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA,” and its notes.
1	09/2009	• In Table 3, “Recommended Operating Conditions,” for $V_{DD_CORE,}$ removed 1.1 ± 55 mV. • In Table 5, “Power Dissipation 5,” remove note 5. • In Table 5, ”Power Dissipation 5,” changed an “—”’ to “0.”
0	08/2009	• Initial public release.